Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

Vishay/Siliconix
SI4406DY-T1-E3

For any questions, you can email us directly:
sales@integrated-circuit.com

Distributor of Vishay/Siliconix: Excellent Integrated System Limited
Datasheet of SI4406DY-T1-E3 - MOSFET N-CH 30V 13A 8-SOIC
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N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
30	0.0045 at V_{GS} = 10 V	20
	0.0055 at V_{GS} = 4.5 V	17

FEATURES

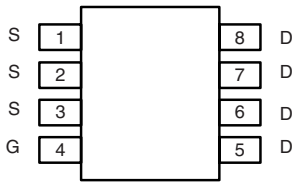
- **Halogen-free According to IEC 61249-2-21 Available**
- TrenchFET® Power MOSFET
- Optimized for "Low Side" Synchronous Rectifier Operation
- 100 % R_g Tested

RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

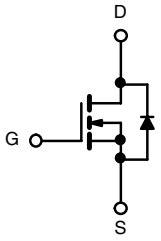
- DC/DC Converters
- Synchronous Rectifiers

SO-8



Top View

Ordering Information: Si4406DY-T1-E3 (Lead (Pb)-free)
Si4406DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**10 s**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	20	13	A
	T_A = 70 °C		15	10	
Pulsed Drain Current (10 µs Pulse Width)		I_{DM}	60		
Continuous Source Current (Diode Conduction)[a]		I_S	2.9	1.3	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	3.5	1.6	W
	T_A = 70 °C		2.2	1	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 10 s	R_{thJA}	29	35	°C/W
	Steady State		67	80	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	13	16	

Notes:
a. Surface Mounted on 1" x 1" FR4 board.

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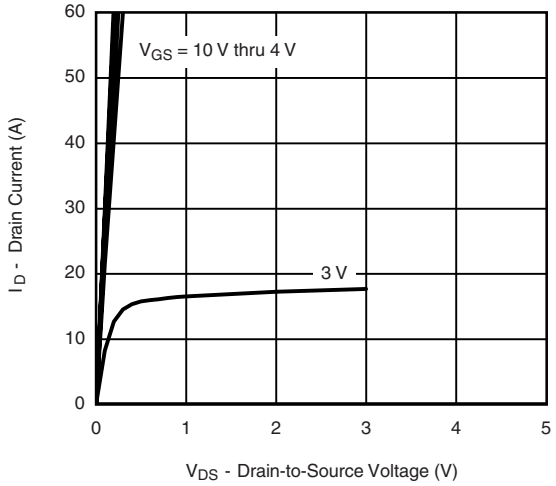
SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1.0	1.95	3.0	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			1	µA
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 55 °C			5	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	30			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		0.0035	0.0045	Ω
		V_{GS} = 4.5 V, I_D = 19 A		0.0043	0.0055	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 20 A		95		S
Diode Forward Voltage[a]	V_{SD}	I_S = 2.9 A, V_{GS} = 0 V		0.72	1.1	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 20 A		34	50	nC
Gate-Source Charge	Q_{gs}			15		
Gate-Drain Charge	Q_{gd}			10		
Gate Resistance	R_g		0.5	1.3	2.2	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 15 Ω I_D ≅ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		21	35	ns
Rise Time	t_r			15	25	
Turn-Off Delay Time	$t_{d(off)}$			100	150	
Fall Time	t_f			30	45	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 2.9 A, dI/dt = 100 A/µs		50	80	

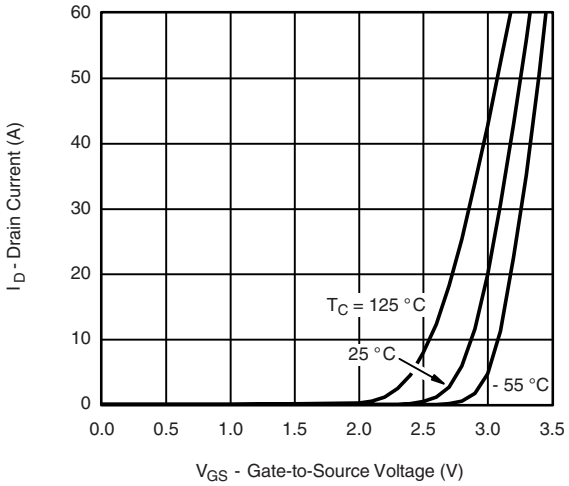
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Output Characteristics



Transfer Characteristics

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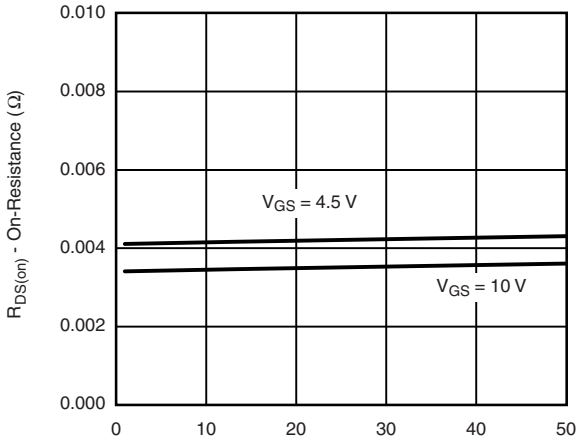
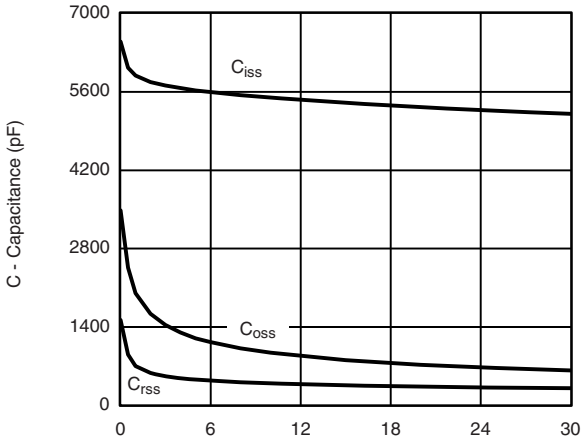
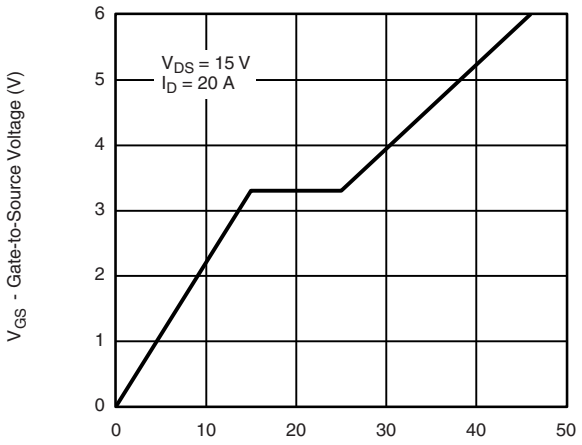


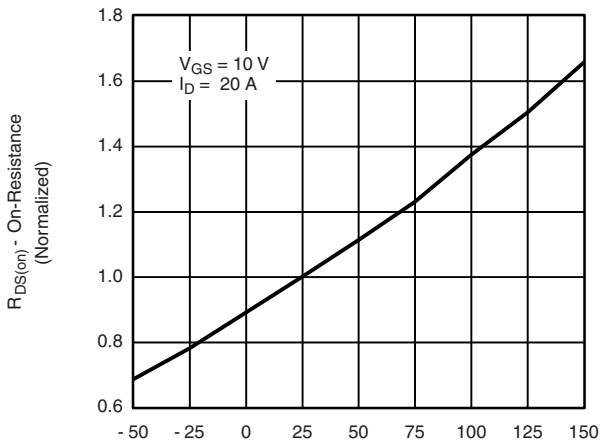
On-Resistance vs. Drain Current



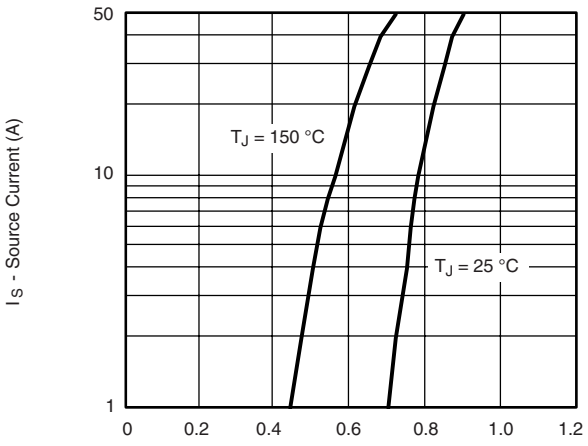
Capacitance



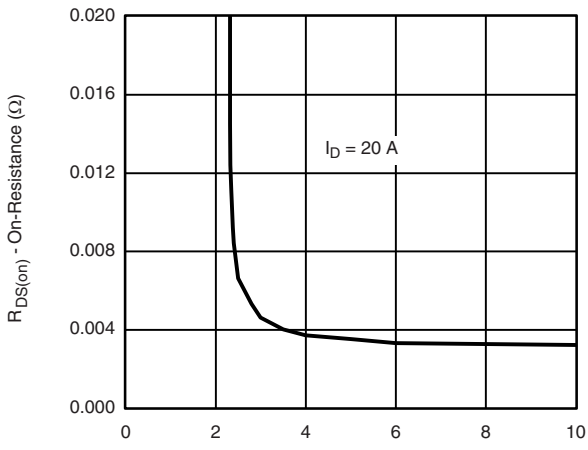
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

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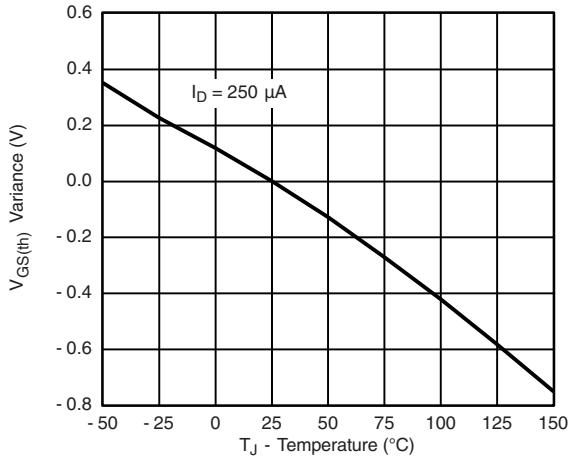
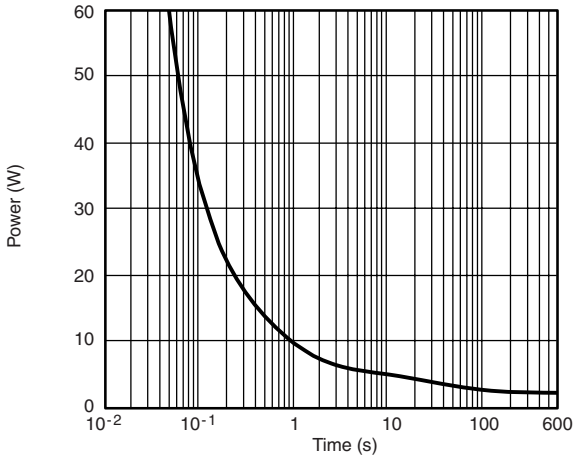
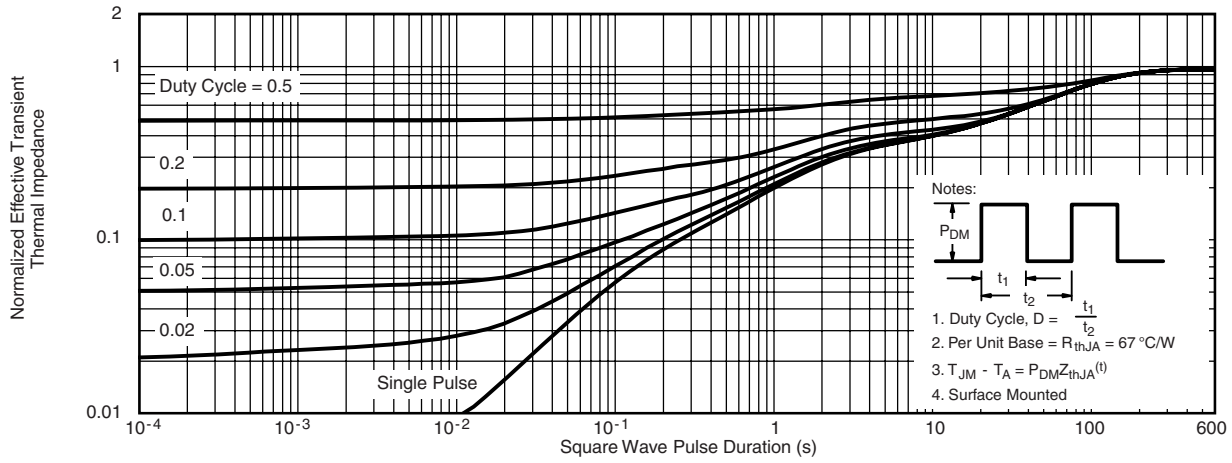


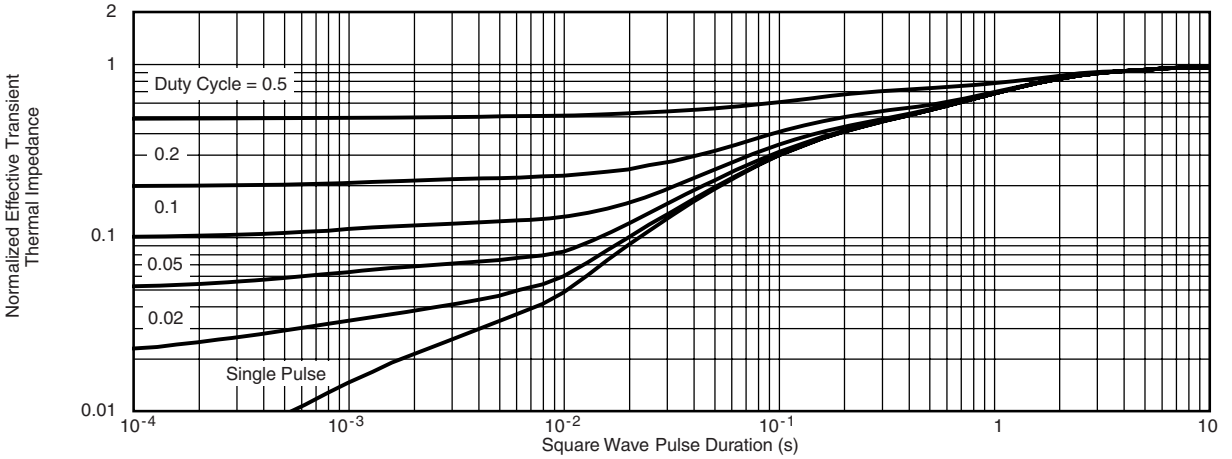
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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